

Silicon NPN Power Transistors

2SC1413

DESCRIPTION

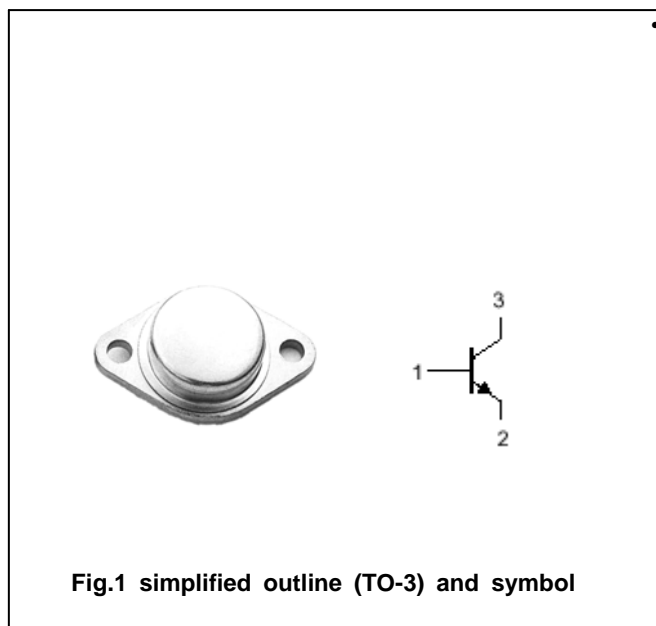
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- For TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings($T_a = ^\circ\text{C}$)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1200	V
V_{CEO}	Collector-emitter voltage	Open base	500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		5	A
P_T	Total power dissipation	$T_C = 25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1.0mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5 A; I _B =1.2 A			10	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5 A; I _B =1.2 A			2	V
I _{CBO}	Collector cut-off current	V _{CB} =1200V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =1A; V _{CE} =5V	8			

PACKAGE OUTLINE

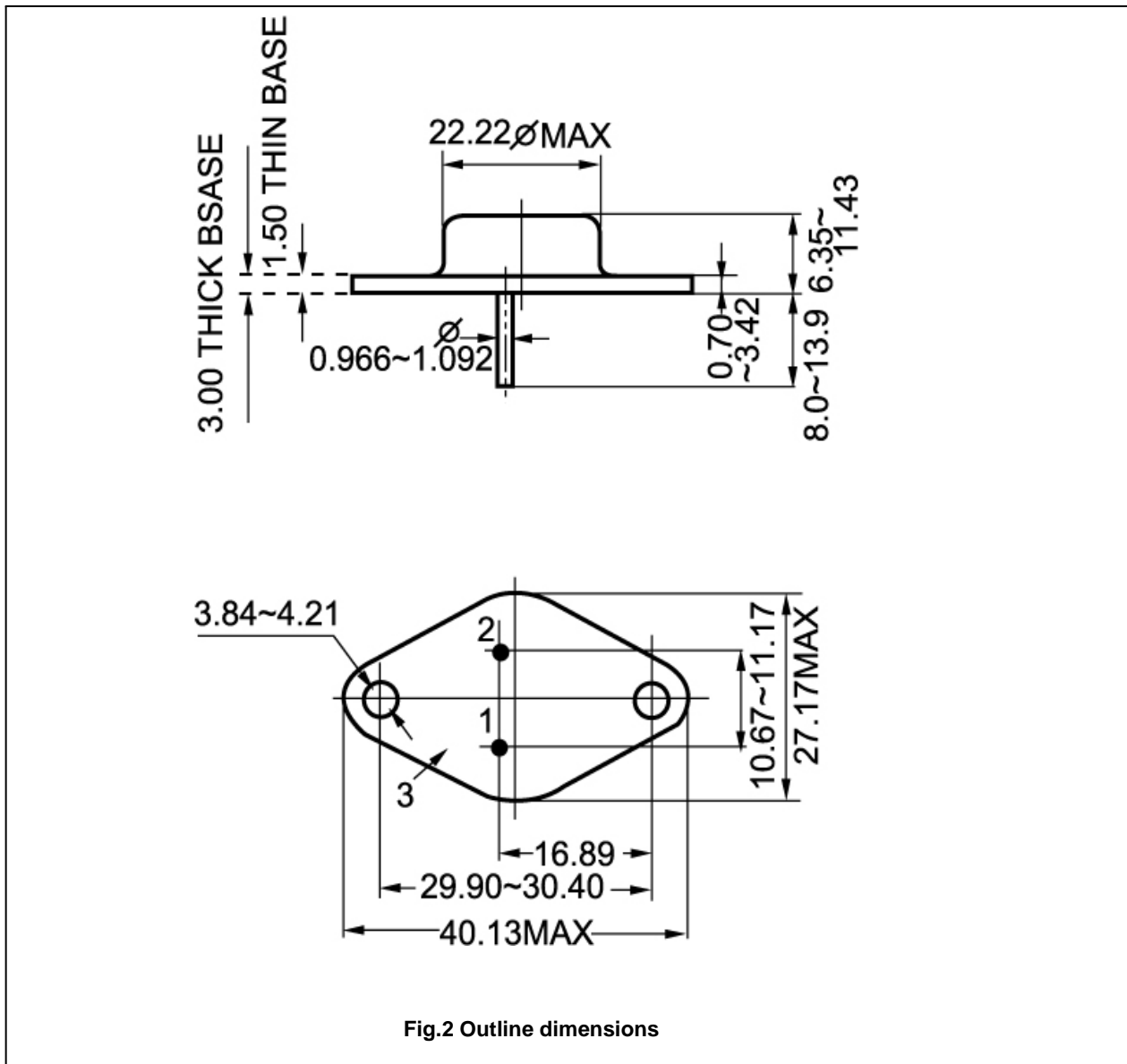


Fig.2 Outline dimensions